

DESCRIPTION

PLASMA PROCESSING APPARATUS AND PLASMA PROCESSING METHOD

5 TECHNICAL FIELD

Sub A-1  
The present invention generally relates to a plasma processing apparatus and, more particularly, to a plasma processing apparatus which applies a magnetic field to a surface of a substrate to which a plasma process is applied and a plasma processing method performed by such a plasma processing apparatus.

BACKGROUND ART

15 Etching of a silicone oxidization film or a polycrystalline silicon film is one of the most important process in production of a semiconductor, and plasma etching has been used as such etching. In order to form a fine pattern of 1.0  $\mu\text{m}$  or less by plasma etching, plasma having an ion current density of 1  $\text{mA}/\text{cm}^2$  or more and an electron density of 1  $10^{10} \text{ cm}^{-3}$  or more is required under a process pressure of 0.5 Pa or less. However, a conventionally used RIE apparatus of a parallel plate type was not able to generate plasma of such conditions.

Sub A-1  
25 In order to achieve the above-mentioned plasma performance, a plasma generating apparatus using a magnetic field has been developed. As an apparatus provided with such a plasma generating apparatus, Japanese Laid-Open Patent Application No. 6-37056 discloses a magnetron plasma etching apparatus using a dipole ring-  
30 magnet.

The magnetron plasma etching apparatus using a dipole-ring magnet is able to generate low pressure and high-density plasma. However, it is difficult to control

09827307 100401

the plasma generated on a substrate with high accuracy. That is, it becomes difficult to attain equalization of the plasma density on a substrate and equalization of a self-bias voltage by introducing a horizontal magnetic  
5 field on the substrate.

As solution which attains equalization of plasma density and a self-bias voltage, a method of giving a slope to a magnetic field (Japanese Laid-Open Patent Application No. 62-21062) or a method of rotating a  
10 magnetic field introduced into a process space (Japanese Laid-Open Patent Application No. 61-208223) is suggested.

945  
A3/ However, the solution suggested in Japanese Laid-Open Patent Application No. 62-21062 has a problem in that the optimum value of a slope magnetic field changes when a  
15 process pressure etc. is changed. Additionally, although the solution suggested in Japanese Laid-Open Patent Application No. 61-208223 apparently achieves equalization of plasma with respect to a substrate being processed, the mechanism for rotating the magnetic field is required, and  
20 there is a problem in that a miniaturization of the whole plasma apparatus is difficult.

In order to solve the above-mentioned problems, the method of equalizing plasma by generating a uniform horizontal magnetic field by applying a high frequency  
25 electric power to an auxiliary electrode. In this solution method, an electron drift is generated in a direction opposite to an electron drift generated on a surface of the substrate placed on a lower electrode so as to promote circulation of electrons in the plasma, which  
30 prevents deviation of electrons. According to this solution, even if it is the case where process pressure etc. is changed, it is possible to attain equalization of plasma by changing the electric power of the radio

09827307 100401

frequency applied to the auxiliary electrode.  
Additionally, since it is not necessary to rotate a magnetic field, it is possible to attain a miniaturization of the plasma apparatus.

5                   However, in association with increase of sizes  
of semiconductor chips such as DRAM or MPU, the diameter  
of the silicone substrate used as a base thereof has  
become large gradually. For example, in order to suppress  
a pressure distribution to less than several percent in  
10 the plasma apparatus which processes a substrate having a  
diameter of 300 mm or more, it is necessary to set a  
distance between the substrate and an upper electrode as  
30 mm or more. In such a distance, diffusion of electrons  
which go from the surface of the substrate to the surface  
15 of the auxiliary electrode and from the auxiliary  
electrode to the surface of the substrate is suppressed.  
As a result, a movement of electrons is prevented and it  
is difficult to equalize the plasma.

                  Additionally, in the conventional sputter  
20 apparatus using a magnetron plasma source, an amount of  
reduction of a target material is uneven, and there is a  
problem in that an efficiency of use of the target is less  
than 50%. In order to solve such a problem, a method of  
using a generally uniform parallel magnetic field is  
25 considered. In such a case, it is necessary to rotate the  
magnetic field or the substrate during a process.  
Therefore, the stress in a thin film formed on the  
substrate spreads to the entire substrate, and there is a  
problem in that the substrate is deformed due to  
30 relaxation of the stress during a machining process as a  
post process. Further, since the surface of the substrate  
is exposed to uneven plasma during film deposition process,  
a control of a film quality on the entire surface of the

09827307-100401

substrate is very difficult. For example, in a sputter apparatus which forms copper wiring, there is a problem in that the resistance of the formed copper wiring is as large as several times of a target value (theoretical value).

15  
16  
17  
18  
19  
20  
21  
22  
23  
24  
25  
26  
27  
28  
29  
30  
31  
32  
33  
34  
35  
36  
37  
38  
39  
40  
41  
42  
43  
44  
45  
46  
47  
48  
49  
50  
51  
52  
53  
54  
55  
56  
57  
58  
59  
60  
61  
62  
63  
64  
65  
66  
67  
68  
69  
70  
71  
72  
73  
74  
75  
76  
77  
78  
79  
80  
81  
82  
83  
84  
85  
86  
87  
88  
89  
90  
91  
92  
93  
94  
95  
96  
97  
98  
99  
100  
101  
102  
103  
104  
105  
106  
107  
108  
109  
110  
111  
112  
113  
114  
115  
116  
117  
118  
119  
120  
121  
122  
123  
124  
125  
126  
127  
128  
129  
130  
131  
132  
133  
134  
135  
136  
137  
138  
139  
140  
141  
142  
143  
144  
145  
146  
147  
148  
149  
150  
151  
152  
153  
154  
155  
156  
157  
158  
159  
160  
161  
162  
163  
164  
165  
166  
167  
168  
169  
170  
171  
172  
173  
174  
175  
176  
177  
178  
179  
180  
181  
182  
183  
184  
185  
186  
187  
188  
189  
190  
191  
192  
193  
194  
195  
196  
197  
198  
199  
200  
201  
202  
203  
204  
205  
206  
207  
208  
209  
210  
211  
212  
213  
214  
215  
216  
217  
218  
219  
220  
221  
222  
223  
224  
225  
226  
227  
228  
229  
230  
231  
232  
233  
234  
235  
236  
237  
238  
239  
240  
241  
242  
243  
244  
245  
246  
247  
248  
249  
250  
251  
252  
253  
254  
255  
256  
257  
258  
259  
260  
261  
262  
263  
264  
265  
266  
267  
268  
269  
270  
271  
272  
273  
274  
275  
276  
277  
278  
279  
280  
281  
282  
283  
284  
285  
286  
287  
288  
289  
290  
291  
292  
293  
294  
295  
296  
297  
298  
299  
300  
301  
302  
303  
304  
305  
306  
307  
308  
309  
310  
311  
312  
313  
314  
315  
316  
317  
318  
319  
320  
321  
322  
323  
324  
325  
326  
327  
328  
329  
330  
331  
332  
333  
334  
335  
336  
337  
338  
339  
340  
341  
342  
343  
344  
345  
346  
347  
348  
349  
350  
351  
352  
353  
354  
355  
356  
357  
358  
359  
360  
361  
362  
363  
364  
365  
366  
367  
368  
369  
370  
371  
372  
373  
374  
375  
376  
377  
378  
379  
380  
381  
382  
383  
384  
385  
386  
387  
388  
389  
390  
391  
392  
393  
394  
395  
396  
397  
398  
399  
400  
401  
402  
403  
404  
405  
406  
407  
408  
409  
410  
411  
412  
413  
414  
415  
416  
417  
418  
419  
420  
421  
422  
423  
424  
425  
426  
427  
428  
429  
430  
431  
432  
433  
434  
435  
436  
437  
438  
439  
440  
441  
442  
443  
444  
445  
446  
447  
448  
449  
450  
451  
452  
453  
454  
455  
456  
457  
458  
459  
460  
461  
462  
463  
464  
465  
466  
467  
468  
469  
470  
471  
472  
473  
474  
475  
476  
477  
478  
479  
480  
481  
482  
483  
484  
485  
486  
487  
488  
489  
490  
491  
492  
493  
494  
495  
496  
497  
498  
499  
500  
501  
502  
503  
504  
505  
506  
507  
508  
509  
510  
511  
512  
513  
514  
515  
516  
517  
518  
519  
520  
521  
522  
523  
524  
525  
526  
527  
528  
529  
530  
531  
532  
533  
534  
535  
536  
537  
538  
539  
540  
541  
542  
543  
544  
545  
546  
547  
548  
549  
550  
551  
552  
553  
554  
555  
556  
557  
558  
559  
560  
561  
562  
563  
564  
565  
566  
567  
568  
569  
570  
571  
572  
573  
574  
575  
576  
577  
578  
579  
580  
581  
582  
583  
584  
585  
586  
587  
588  
589  
590  
591  
592  
593  
594  
595  
596  
597  
598  
599  
600  
601  
602  
603  
604  
605  
606  
607  
608  
609  
610  
611  
612  
613  
614  
615  
616  
617  
618  
619  
620  
621  
622  
623  
624  
625  
626  
627  
628  
629  
630  
631  
632  
633  
634  
635  
636  
637  
638  
639  
640  
641  
642  
643  
644  
645  
646  
647  
648  
649  
650  
651  
652  
653  
654  
655  
656  
657  
658  
659  
660  
661  
662  
663  
664  
665  
666  
667  
668  
669  
670  
671  
672  
673  
674  
675  
676  
677  
678  
679  
680  
681  
682  
683  
684  
685  
686  
687  
688  
689  
690  
691  
692  
693  
694  
695  
696  
697  
698  
699  
700  
701  
702  
703  
704  
705  
706  
707  
708  
709  
710  
711  
712  
713  
714  
715  
716  
717  
718  
719  
720  
721  
722  
723  
724  
725  
726  
727  
728  
729  
730  
731  
732  
733  
734  
735  
736  
737  
738  
739  
740  
741  
742  
743  
744  
745  
746  
747  
748  
749  
750  
751  
752  
753  
754  
755  
756  
757  
758  
759  
760  
761  
762  
763  
764  
765  
766  
767  
768  
769  
770  
771  
772  
773  
774  
775  
776  
777  
778  
779  
780  
781  
782  
783  
784  
785  
786  
787  
788  
789  
790  
791  
792  
793  
794  
795  
796  
797  
798  
799  
800  
801  
802  
803  
804  
805  
806  
807  
808  
809  
810  
811  
812  
813  
814  
815  
816  
817  
818  
819  
820  
821  
822  
823  
824  
825  
826  
827  
828  
829  
830  
831  
832  
833  
834  
835  
836  
837  
838  
839  
840  
841  
842  
843  
844  
845  
846  
847  
848  
849  
850  
851  
852  
853  
854  
855  
856  
857  
858  
859  
860  
861  
862  
863  
864  
865  
866  
867  
868  
869  
870  
871  
872  
873  
874  
875  
876  
877  
878  
879  
880  
881  
882  
883  
884  
885  
886  
887  
888  
889  
890  
891  
892  
893  
894  
895  
896  
897  
898  
899  
900  
901  
902  
903  
904  
905  
906  
907  
908  
909  
910  
911  
912  
913  
914  
915  
916  
917  
918  
919  
920  
921  
922  
923  
924  
925  
926  
927  
928  
929  
930  
931  
932  
933  
934  
935  
936  
937  
938  
939  
940  
941  
942  
943  
944  
945  
946  
947  
948  
949  
950  
951  
952  
953  
954  
955  
956  
957  
958  
959  
960  
961  
962  
963  
964  
965  
966  
967  
968  
969  
970  
971  
972  
973  
974  
975  
976  
977  
978  
979  
980  
981  
982  
983  
984  
985  
986  
987  
988  
989  
990  
991  
992  
993  
994  
995  
996  
997  
998  
999  
1000  
1001  
1002  
1003  
1004  
1005  
1006  
1007  
1008  
1009  
1010  
1011  
1012  
1013  
1014  
1015  
1016  
1017  
1018  
1019  
1020  
1021  
1022  
1023  
1024  
1025  
1026  
1027  
1028  
1029  
1030  
1031  
1032  
1033  
1034  
1035  
1036  
1037  
1038  
1039  
1040  
1041  
1042  
1043  
1044  
1045  
1046  
1047  
1048  
1049  
1050  
1051  
1052  
1053  
1054  
1055  
1056  
1057  
1058  
1059  
1060  
1061  
1062  
1063  
1064  
1065  
1066  
1067  
1068  
1069  
1070  
1071  
1072  
1073  
1074  
1075  
1076  
1077  
1078  
1079  
1080  
1081  
1082  
1083  
1084  
1085  
1086  
1087  
1088  
1089  
1090  
1091  
1092  
1093  
1094  
1095  
1096  
1097  
1098  
1099  
1100  
1101  
1102  
1103  
1104  
1105  
1106  
1107  
1108  
1109  
1110  
1111  
1112  
1113  
1114  
1115  
1116  
1117  
1118  
1119  
1120  
1121  
1122  
1123  
1124  
1125  
1126  
1127  
1128  
1129  
1130  
1131  
1132  
1133  
1134  
1135  
1136  
1137  
1138  
1139  
1140  
1141  
1142  
1143  
1144  
1145  
1146  
1147  
1148  
1149  
1150  
1151  
1152  
1153  
1154  
1155  
1156  
1157  
1158  
1159  
1160  
1161  
1162  
1163  
1164  
1165  
1166  
1167  
1168  
1169  
1170  
1171  
1172  
1173  
1174  
1175  
1176  
1177  
1178  
1179  
1180  
1181  
1182  
1183  
1184  
1185  
1186  
1187  
1188  
1189  
1190  
1191  
1192  
1193  
1194  
1195  
1196  
1197  
1198  
1199  
1200  
1201  
1202  
1203  
1204  
1205  
1206  
1207  
1208  
1209  
1210  
1211  
1212  
1213  
1214  
1215  
1216  
1217  
1218  
1219  
1220  
1221  
1222  
1223  
1224  
1225  
1226  
1227  
1228  
1229  
1230  
1231  
1232  
1233  
1234  
1235  
1236  
1237  
1238  
1239  
1240  
1241  
1242  
1243  
1244  
1245  
1246  
1247  
1248  
1249  
1250  
1251  
1252  
1253  
1254  
1255  
1256  
1257  
1258  
1259  
1260  
1261  
1262  
1263  
1264  
1265  
1266  
1267  
1268  
1269  
1270  
1271  
1272  
1273  
1274  
1275  
1276  
1277  
1278  
1279  
1280  
1281  
1282  
1283  
1284  
1285  
1286  
1287  
1288  
1289  
1290  
1291  
1292  
1293  
1294  
1295  
1296  
1297  
1298  
1299  
1300  
1301  
1302  
1303  
1304  
1305  
1306  
1307  
1308  
1309  
1310  
1311  
1312  
1313  
1314  
1315  
1316  
1317  
1318  
1319  
1320  
1321  
1322  
1323  
1324  
1325  
1326  
1327  
1328  
1329  
1330  
1331  
1332  
1333  
1334  
1335  
1336  
1337  
1338  
1339  
1340  
1341  
1342  
1343  
1344  
1345  
1346  
1347  
1348  
1349  
1350  
1351  
1352  
1353  
1354  
1355  
1356  
1357  
1358  
1359  
1360  
1361  
1362  
1363  
1364  
1365  
1366  
1367  
1368  
1369  
1370  
1371  
1372  
1373  
1374  
1375  
1376  
1377  
1378  
1379  
1380  
1381  
1382  
1383  
1384  
1385  
1386  
1387  
1388  
1389  
1390  
1391  
1392  
1393  
1394  
1395  
1396  
1397  
1398  
1399  
1400  
1401  
1402  
1403  
1404  
1405  
1406  
1407  
1408  
1409  
1410  
1411  
1412  
1413  
1414  
1415  
1416  
1417  
1418  
1419  
1420  
1421  
1422  
1423  
1424  
1425  
1426  
1427  
1428  
1429  
1430  
1431  
1432  
1433  
1434  
1435  
1436  
1437  
1438  
1439  
1440  
1441  
1442  
1443  
1444  
1445  
1446  
1447  
1448  
1449  
1450  
1451  
1452  
1453  
1454  
1455  
1456  
1457  
1458  
1459  
1460  
1461  
1462  
1463  
1464  
1465  
1466  
1467  
1468  
1469  
1470  
1471  
1472  
1473  
1474  
1475  
1476  
1477  
1478  
1479  
1480  
1481  
1482  
1483  
1484  
1485  
1486  
1487  
1488  
1489  
1490  
1491  
1492  
1493  
1494  
1495  
1496  
1497  
1498  
1499  
1500  
1501  
1502  
1503  
1504  
1505  
1506  
1507  
1508  
1509  
1510  
1511  
1512  
1513  
1514  
1515  
1516  
1517  
1518  
1519  
1520  
1521  
1522  
1523  
1524  
1525  
1526  
1527  
1528  
1529  
1530  
1531  
1532  
1533  
1534  
1535  
1536  
1537  
1538  
1539  
1540  
1541  
1542  
1543  
1544  
1545  
1546  
1547  
1548  
1549  
1550  
1551  
1552  
1553  
1554  
1555  
1556  
1557  
1558  
1559  
1560  
1561  
1562  
1563  
1564  
1565  
1566  
1567  
1568  
1569  
1570  
1571  
1572  
1573  
1574  
1575  
1576  
1577  
1578  
1579  
1580  
1581  
1582  
1583  
1584  
1585  
1586  
1587  
1588  
1589  
1590  
1591  
1592  
1593  
1594  
1595  
1596  
1597  
1598  
1599  
1600  
1601  
1602  
1603  
1604  
1605  
1606  
1607  
1608  
1609  
1610  
1611  
1612  
1613  
1614  
1615  
1616  
1617  
1618  
1619  
1620  
1621  
1622  
1623  
1624  
1625  
1626  
1627  
1628  
1629  
1630  
1631  
1632  
1633  
1634  
1635  
1636  
1637  
1638  
1639  
1640  
1641  
1642  
1643  
1644  
1645  
1646  
1647  
1648  
1649  
1650  
1651  
1652  
1653  
1654  
1655  
1656  
1657  
1658  
1659  
1660  
1661  
1662  
1663  
1664  
1665  
1666  
1667  
1668  
1669  
1670  
1671  
1672  
1673  
1674  
1675  
1676  
1677  
1678  
1679  
1680  
1681  
1682  
1683  
1684  
1685  
1686  
1687  
1688  
1689  
1690  
1691  
1692  
1693  
1694  
1695  
1696  
1697  
1698  
1699  
1700  
1701  
1702  
1703  
1704  
1705  
1706  
1707  
1708  
1709  
1710  
1711  
1712  
1713  
1714  
1715  
1716  
1717  
1718  
1719  
1720  
1721  
1722  
1723  
1724  
1725  
1726  
1727  
1728  
1729  
1730  
1731  
1732  
1733  
1734  
1735  
1736  
1737  
1738  
1739  
1740  
1741  
1742  
1743  
1744  
1745  
1746  
1747  
1748  
1749  
1750  
1751  
1752  
1753  
1754  
1755  
1756  
1757  
1758  
1759  
1760  
1761  
1762  
1763  
1764  
1765  
1766  
1767  
1768  
1769  
1770  
1771  
1772  
1773  
1774  
1775  
1776  
1777  
1778  
1779  
1780  
1781  
1782  
1783  
1784  
1785  
1786  
1787  
1788  
1789  
1790  
1791  
1792  
1793  
1794  
1795  
1796  
1797  
1798  
1799  
1800  
1801  
1802  
1803  
1804  
1805  
1806  
1807  
1808  
1809  
1810  
1811  
1812  
1813  
1814  
1815  
1816  
1817  
1818  
1819  
1820  
1821  
1822  
1823  
1824  
1825  
1826  
1827  
1828  
1829  
1830  
1831  
1832  
1833  
1834  
1835  
1836  
1837  
1838  
1839  
1840  
1841  
1842  
1843  
1844  
1845  
1846  
1847  
1848  
1849  
1850  
1851  
1852  
1853  
1854  
1855  
1856  
1857  
1858  
1859  
1860  
1861  
1862  
1863  
1864  
1865  
1866  
1867  
1868  
1869  
1870  
1871  
1872  
1873  
1874  
1875  
1876  
1877  
1878  
1879  
1880  
1881  
1882  
1883  
1884  
1885  
1886  
1887  
1888  
1889  
1890  
1891  
1892  
1893  
1894  
1895  
1896  
1897  
1898  
1899  
1900  
1901  
1902  
1903  
1904  
1905  
1906  
1907  
1908  
1909  
1910  
1911  
1912  
1913  
1914  
1915  
1916  
1917  
1918  
1919  
1920  
1921  
1922  
1923  
1924  
1925  
1926  
1927  
1928  
1929  
1930  
1931  
1932  
1933  
1934  
1935  
1936  
1937  
1938  
1939  
1940  
1941  
1942  
1943  
1944  
1945  
1946  
1947  
1948  
1949  
1950  
1951  
1952  
1953  
1954  
1955  
1956  
1957  
1958  
1959  
1960  
1961  
1962  
1963  
1964  
1965  
1966  
1967  
1968  
1969  
1970  
1971  
1972  
1973  
1974  
1975  
1976  
1977  
1978  
1979  
1980  
1981  
1982  
1983  
1984  
1985  
1986  
1987  
1988  
1989  
1990  
1991  
1992  
1993  
1994  
1995  
1996  
1997  
1998  
1999  
2000  
2001  
2002  
2003  
2004  
2005  
2006  
2007  
2008  
2009  
2010  
2011  
2012  
2013  
2014  
2015  
2016  
2017  
2018  
2019  
2020  
2021  
2022  
2023  
2024  
2025  
2026  
2027  
2028  
2029  
2030  
2031  
2032  
2033  
2034  
2035  
2036  
2037  
2038  
2039  
2040  
2041  
2042  
2043  
2044  
2045  
2046  
2047  
2048  
2049  
2050  
2051  
2052  
2053  
2054  
2055  
2056  
2057  
2058  
2059  
2060  
2061  
2062  
2063  
2064  
2065  
2066  
2067  
2068  
2069  
2070  
2071  
2072  
2073  
2074  
2075  
2076  
2077  
2078  
2079  
2080  
2081  
2082  
2083  
2084  
2085  
2086  
2087  
2088  
2089  
2090  
2091  
2092  
2093  
2094  
2095  
2096  
2097  
2098  
2099  
2100  
2101  
2102  
2103  
2104  
2105  
2106  
2107  
2108  
2109  
2110  
2111  
2112  
2113  
2114  
2115  
2116  
2117  
2118  
2119  
2120  
2121  
2122  
2123  
2124  
2125  
2126  
2127  
2128  
2129  
2130  
2131  
2132  
2133  
2134  
2135  
2136  
2137  
2138  
2139  
2140  
2141  
2142  
2143  
2144  
2145  
2146  
2147  
2148  
2149  
2150  
2151  
2152  
2153  
2154  
2155  
2156  
2157  
2158  
2159  
2160  
2161  
2162  
2163  
2164  
2165  
2166  
2167  
2168  
2169  
2170  
2171  
2172  
2173  
2174  
2175  
2176  
2177  
2178  
2179  
2180  
2181  
2182  
2183  
2184  
2185  
2186  
2187  
2188  
2189  
2190  
2191  
2192  
2193  
2194  
2195  
2196  
2197  
2198  
2199  
2200  
2201  
2202  
2203  
2204  
2205  
2206  
2207  
2208  
2209  
2210  
2211  
2212  
2213  
2214  
2215  
2216  
2217  
2218  
2219  
2220  
2221  
2222  
2223  
2224  
2225  
2226  
2227  
2228  
2229  
2230  
2231  
2232  
2233

as to cause electrons in the plasma to drift from a front surface to a back surface of the auxiliary electrode and from the back surface to the front surface of the auxiliary electrode.

5 The front surface of the auxiliary electrode may be covered by an insulating material. Additionally, it is preferable that a level of a surface of the substrate placed on the first electrode and a level of the front surface of the auxiliary electrode are equal to each other or within  $\pm 2$  mm. The magnetic field applying means may comprise a dipole ring-magnet. It is preferable that a frequency  $f_1$  of a radio frequency applied to the first electrode and a frequency  $f_2$  of a radio frequency applied to the auxiliary electrode are equal to each other and  
10 phases thereof are different from each other. Further, it is preferable that a frequency  $f_2$  of a radio frequency applied to the auxiliary electrode is higher than a frequency  $f_1$  of a radio frequency applied to the first electrode ( $f_2 > f_1$ ).

15 Other objects, features and advantages of the present invention will become more apparent from the following detailed description when read in conjunction with the accompanying drawings.

## 25 BRIEF DESCRIPTION OF DRAWINGS

FIG. 1 is a structural diagram of a plasma processing apparatus according to a first embodiment of the present invention.

FIG. 2 is a perspective view of a substrate, a first electrode and an auxiliary electrode of the plasma processing apparatus shown in FIG. 1.

FIG. 3 is a plane view of the auxiliary electrode.

09827307-100401

FIG. 4 is a plane view showing a variation of the auxiliary electrode.

FIG. 5 is a graph showing a self-bias potential measured in the plasma processing apparatus according to the first embodiment of the present invention.

FIG. 6 is a graph showing an ion current density measured in the plasma processing apparatus according to the first embodiment of the present invention.

FIG. 7 is a structural diagram of a plasma sputter film deposition apparatus according to a second embodiment of the present invention.

FIG. 8 is a cross-sectional view of an auxiliary electrode in a third embodiment of the present invention.

FIG. 9 is a graph showing a radio frequency electric power applied to an auxiliary electrode, which can make a self-bias potential the most uniform in cases where a surface of the auxiliary electrode is covered or not covered by an insulating material.

FIG. 10 is a graph showing an amount of consumption of an inner wall of a process chamber.

FIG. 11 is a graph showing a result of measurement of an amount of consumption of the auxiliary electrode by applying a radio frequency electric power, of which frequency is higher than a radio frequency electric power applied to the first electrode, to the auxiliary electrode.

FIG. 12 is a graph showing a change in the radio frequency electric power applied to the auxiliary electrode needed to uniform the self-bias potential by a difference in a height between an upper surface of the first electrode and an upper surface of the auxiliary electrode.

FIG. 13 is an illustration showing an action of

09827307.100401

an electron drift when the surface of the first electrode is higher than the surface of the auxiliary electrode.

FIG. 14 is an illustration showing an action of an electron drift when the surface of the first electrode is lower than the surface of the auxiliary electrode.

~~BEST MODE FOR CARRYING OUT THE INVENTION~~

A description will be given below, with reference to the drawings, of embodiments of the present invention.

FIG. 1 is a structural diagram of a plasma processing apparatus according to a first embodiment of the present invention. In the plasma processing apparatus shown in FIG. 1, a substrate 101 to which a plasma process is applied is placed on an electrode 102. A plasma process applied to the substrate 101 by exciting plasma on the surface of the substrate 101. The dipole ring-magnet 103 is provided in the circumference of a process chamber 108 in which the substrate 101 is accommodated as a means to apply a magnetic field. As a means to apply a magnetic field, although a permanent magnet or an electromagnet may be used, it is preferable to use a dipole ring-magnet when installation capacity, electric power consumption, magnetic field leakage, etc. are taken into consideration.

An auxiliary electrode 104 is installed on an outer periphery of the first electrode 102. The auxiliary electrode may surround the entire periphery or a part of the periphery of the first electrode 102. The auxiliary electrode 104 is provided so as to excite plasma in the vicinity of the back surface 105 and the front surface 106 thereof.

FIG. 2 is a perspective view of the substrate 101, the first electrode 102 and the auxiliary electrode

09827307-100401

104 of the plasma processing apparatus shown in FIG. 1.  
An arrow 204 shows the drift of electrons to the front  
surface 106 from the back surface 105 of the auxiliary  
electrode 104, and an arrow 205 shows the drift of  
5 electrons to the back surface 105 from the front surface  
106 of the auxiliary electrode 104. An arrow 206  
indicated by the dotted line shows the drift of electrons  
in the vicinity of the back surface 105 of the auxiliary  
electrode 104, and an arrow 207 shows the drift of  
10 electrons in the vicinity of the surface of the substrate  
101 and the front surface 106 of the auxiliary electrode  
104. The drift of electrons indicated by arrows 204, 205,  
206 and 207 is generated by the interaction of a magnetic  
field or a magnetic field and substrate and a sheath  
15 electrode generated between the substrate and the  
auxiliary electrode.

In the conventional magnetron plasma apparatus,  
the drift of electrons shown by arrows 204, 205 and 206  
hardly occurs, but only the drift of electrons shown by  
20 the arrow 207 occurs. For this reason, electrons in the  
plasma shift toward the W-pole, which results in  
generation of uneven plasma.

In the plasma processing apparatus according to  
the present embodiment, electrons generated by the surface  
25 of the substrate 101 and the auxiliary electrode 104 flow  
according to the electron drift on the surface of the  
substrate and the front surface of the auxiliary electrode  
104 (indicated by the arrow 207, the electron drift from  
the front surface 106 to the back surface 105 of the  
30 auxiliary electrode 104 (indicated by the arrow 205), the  
electron drift on the back surface 106 of the auxiliary  
electrode 104 (indicated by the arrow 206), the electron  
drift from the back surface 105 to the front surface 106

09827307.100401



of the auxiliary electrode 104 (indicated by the arrow 204) and diffusion movement of electrons. According to the flow of electrons, electrons in the plasma are prevented from moving in a certain direction of the applied magnetic field, thereby achieving uniformization of the entire plasma.

As mentioned above, the plasma processing apparatus shown in FIG. 1 comprises: the first electrode 102 on which the substrate 101 to which a plasma process is applied is placed; the magnetic field applying means 103 for applying a magnetic field to the surface to which the plasma process is applied; and the auxiliary electrode 104 provided on an outer periphery of the first electrode 102, wherein electrons in the plasma is caused to drift from the front surface 106 to the back surface 105 of the auxiliary electrode 104 and from the back surface 105 to the front surface 106 of the auxiliary electrode 104 by exciting plasma on the front surface 106 and the back surface 105 of the auxiliary electrode 104.

A description will now be given of a structure of the plasma processing apparatus shown in FIG. 1 in the case of using the plasma processing apparatus as a plasma etching apparatus. The process chamber 108 shown in FIG. 1 is made of aluminum, and the turbo-molecular pump 302 is provided on the bottom thereof as an exhaust means. The turbo-molecular pump 302 exhausts and depressurizes the gas from inside a chamber 301. Additionally, a gas introduction port is provided in the process chamber 108 as a gas introduction means so as to introduce gas, such as  $C_4F_8$ , carbon monoxide, oxygen or xenon, into process chamber 108 through the gas introduction port 303. The inside of the process chamber 108 is maintained at a desired pressure by the introduction of the gas and the

09827307.100401

exhaust of the gas by the turbo numerator pump 302. The combination of the above-mentioned gases is not limited to the above mentioned combination, and as other examples there are  $C_4F_8$ , carbon monoxide, oxygen, argon, etc.

5. Additionally, since  $C_4F_8$ , carbon monoxide, oxygen and xenon are preferable since they suppresses an excessive dissociation of gas and improve the etching characteristic.

The first electrode 102 is connected to a radio frequency power supply 306 having a frequency of 13.56 MHz via a matching circuit 305. Although the frequency of the radio frequency power supply can also be set to 27.12 MHz or 40 MHz, a radio frequency of about 13.56 MHz is preferable, when etching of an oxidization film is performed, at which a self-bias potential of the plasma becomes large. In etching of an insulated film, it is preferable to set a high self-bias at an initial stage so as to etch at a high speed, and to set a low self-bias at an etching end stage. Accordingly, a damage of the background of the insulated film can be reduced.

20. A grounded second electrode 307 is provided above the first electrode 102. Although parallel plate type electrode is used as the second electrode 307 in the present embodiment, a plasma source electrode such as a multi-target type, a microwave excitation type, an electron cyclotron resonance type or an induction coupling type may be used. In order to improve the etching characteristic, the parallel plate type is preferable. The substrate 101 of silicon which has a silicon oxidization film is placed on the surface of the first electrode 102.

The auxiliary electrode 104 is connected to a radio frequency power supply 311 having a frequency of 100 MHz via a matching circuit 310. The magnetic field

09827307-100401

applying means 103 in the present embodiment is a dipole ring-magnet of 12 mT (120 Gausses).

FIG. 3 is a plan view of the auxiliary electrode 104. Although the ring-shaped auxiliary electrode 104 is used in the present embodiment, the auxiliary electrode 104 may be divided into four parts like an auxiliary electrode 104A as shown in FIG. 4. In this case, a distance D between the divided parts is preferably within 2 mm which is within an electron cycloid radius.

As shown in FIG. 2, by arranging the auxiliary electrode 104 on the outer periphery of the first electrode 102, the drift (indicated by the arrow 207) of electrons from the E-pole to the W-pole in the applied magnetic field occurs on the surface of the substrate 101 and the front surface 106 of the auxiliary electrode 104, and the drift (indicated by the arrow 206) of electrons from the W-pole to the E-pole of the applied magnetic field occurs on the back surface 105 of the auxiliary electrode 104. Moreover, on the W-pole side of the auxiliary electrode 104, the drift (indicated by the arrow 205) of electrons from the back surface 105 to the front surface 106 occurs, and the drift (indicated by the arrow 204) of electrons from the back surface 105 to the front surface occurs on the E-pole side of the auxiliary electrode 104. By such electron drift, deviation of electrons can be prevented by the electron being caused to flow, and uniformization of plasma is achieved.

FIG. 5 is a graph showing the self-bias potential-measured in the plasma processing apparatus according to the present embodiment. Measurements were taken for the case where the auxiliary electrode 104 is provided and the case where the auxiliary electrode 104 is not provided. In the case where the auxiliary electrode

09827307-100401

104 is not provided, the structure is the same as that of a regular magnetron plasma apparatus. As appreciated from FIG. 5, when the auxiliary electrode 104 was not provided, a self-bias potential difference of 20 V occurred between the E-pole side and the W-pole side on the substrate. However, self-bias potential difference was able to be set to 2 V by providing the auxiliary electrode 104 on the outer periphery of the first electrode 102 as in the present embodiment.

FIG. 6 is a graph showing an ion current density measured in the plasma processing apparatus according to the present embodiment. When the auxiliary electrode 104 was not provided, the ion current density dropped extremely on the E-pole side. However, like the present embodiment, by providing the auxiliary electrode 104 on the outer periphery of the first electrode, the drop of the ion current on the side of the E-pole was able to be eliminated, and was able to achieve a uniform ion current density on the substrate.

Using the plasma etching apparatus according to the present invention, a silicon substrate was etched by introducing a mixed gas of  $C_4F_8$ , carbon monoxide, oxygen, and xenon into the process chamber 108 and setting the chamber pressure to 5 Pa. The silicone substrate had a silicone oxidization film with a thickness of 1.6 micrometers formed on the surface thereof, and the diameter was 200 mm. When a radio frequency electric power of 1500 W was supplied to the first electrode 102 and a high frequency electric power of 200 W was supplied to the auxiliary electrode 104, the uniformity of the etching rate was  $\pm 2\%$ .

A description will now be given, with reference to FIG. 7, of a second embodiment of the present invention.

09827307-100401

FIG. 7 is a structural diagram of a plasma sputtering apparatus according to the second embodiment of the present invention. In FIG. 7, parts that are the same as the parts shown in FIG. 1 are given the same reference numerals, and descriptions thereof will be omitted.

The process chamber 108 shown in FIG. 7 is made of aluminum, and a protective film is provided by forming an aluminum fluoride by applying a fluoride treatment to an inner surface thereof. The process chamber 108 is not limited to such a structure, and it is preferable to form an inner wall which discharges an extremely small amount of gas such as water other than a process gas. Similar to the plasma processing apparatus shown in FIG. 1, the inside of the process chamber 108 is depressurized by using the turbo-molecular pump 302. Additionally, argon gas is introduced into the process chamber 108 from the gas supply passage 803 as a gas introduction means. The gas to be used is not limited to argon gas, and a mixture gas of xenon or krypton and oxygen may be used. Argon is preferable for a copper sputtering film deposition.

The first electrode 102 is connected to the radio frequency power supply 306 having a frequency of 13.56 MHz via the matching circuit 305. The frequency of the radio frequency power supply 306 is not limited to this frequency and 27.12 MHz or 40 MHz may be used. As for sputtering, a frequency near 13.56 MHz is preferable at which the self-bias potential generated on the target surface becomes large. A substrate 807 as a copper target is attached to a surface of the first electrode 102. Although the copper target is used in the present embodiment, the target is not limited to copper and a material to be deposited can be attached as the target. The auxiliary electrode 104 is connected to the radio

09027307-100401

frequency power supply 311 having a frequency of 100 MHz via the matching circuit 310. The dipole ring-magnet 103 of 12 mTs (120 Gausses) is used as a magnetic field applying means.

5                   A second electrode 812 is arranged in the position, which counters with first electrode 102. A silicon substrate 813 having a surface on which a silicone oxidization film is formed is placed on the second electrode 812. Additionally, the second electrode 812 is  
10 connected to a radio frequency power supply 815 having a frequency of 40 MHz via a matching circuit 814. The frequency of the radio frequency power supply 815 is not limited to this frequency, and 13.56 MHz or 27.12 MHz may be used. A higher frequency is preferable in order to  
15 increase the quantity of ions which irradiate the silicon substrate and to reduce the self-bias potential to be generated.

Copper sputtering was performed on the silicone substrate 813 by using the sputtering apparatus according  
20 to the present embodiment. Argon gas was introduced into the process chamber 108 and the pressure was set to 0.1 Pa. A radio frequency electric power of 1500 W was supplied to the first electrode 102, and a radio frequency electric power of 200 W was supplied to the auxiliary electrode 104.  
25 Consequently, a copper thin film was formed on the substrate 813, which film has no stress at all and has a film thickness uniformity of  $\pm 2\%$  and a resistivity of  $2.76 \mu\Omega$ .

--A description will now be given of a plasma  
30 etching apparatus according to a third embodiment of the present invention. The plasma processing apparatus according to the third embodiment of the present invention is provided with an auxiliary electrode having a surface

09827307-100401

covered by an insulating material instead of the auxiliary electrode 104.

FIG. 8 is a cross-sectional view of an auxiliary electrode 901 in the present embodiment. The auxiliary electrode 901 has an insulator 902 formed on the surface 106 of the auxiliary electrode 104. In the present embodiment, although the insulator 902 is formed of aluminum nitride AlN, it can be formed of quartz, alumina, Teflon, polyimide, etc. AlN is preferable because of a high thermal conductivity and a high plasma resistance. It should be noted that other parts of the auxiliary electrode 901 are the same as the parts shown in FIG. 1, and descriptions thereof will be omitted.

FIG. 9 is a graph showing a radio frequency electric power applied to the auxiliary electrode, which can make a self-bias potential the most uniform in cases where a surface of the auxiliary electrode is covered or not covered by an insulating material. When the surface of the auxiliary electrode was not covered by an insulator, the radio frequency electric power which can make a self-bias potential uniform was 200 W. On the other hand, it was 100 W when covered by an insulator.

Using the plasma etching apparatus according to the present embodiment, a silicon substrate was etched by introducing a mixed gas of  $C_4F_8$ , carbon monoxide, oxygen, and xenon into the process chamber 108 and setting the chamber pressure to 5 Pa. The silicone substrate had a silicone oxidization film with a thickness of 1.6  $\mu m$  formed on the surface thereof, and the diameter was 200 mm. A radio frequency electric power of 1500 W was supplied to the first electrode 102 and a high frequency electric power of 200 W was supplied to the auxiliary electrode 104. As a result, the uniformity of the etching rate was  $\pm 2\%$ .

09827307-100401

A further detailed description will be given of a result of measurement with respect to the plasma etching apparatus according to the above-mentioned first embodiment.

5 First, a description will be given of a case in which a radio frequency electric power having a frequency of 13.56 MHz, which is the same as the radio frequency electric power supplied to the first electrode 102, is supplied to the auxiliary electrode 104 while varying the  
10 phase from 0 degree to 180 degrees.

FIG. 10 is a graph showing an amount of consumption of the inner wall of the process chamber in the above-mentioned condition. After exciting plasma for 24 hours, change of the thickness in the inner wall of the  
15 process chamber was measured. In a case where a radio frequency of 13.56 MHz was applied to the first electrode 102 in phase of 0 degree, the thickness of the chamber decreased by 30  $\mu\text{m}$ . On the other hand, when the radio frequency was applied with antiphase of 180 degrees, the  
20 thickness of the chamber decreased by 7  $\mu\text{m}$ , and there was least reduction of the thickness of the chamber.

Additionally, using the plasma etching apparatus according to the present embodiment, a silicon substrate was etched 300 times by introducing a mixed gas of  $\text{C}_4\text{F}_8$ ,  
25 carbon monoxide, oxygen, and xenon into the process chamber and setting the pressure to 5 Pa, the silicone substrate having a silicone oxidization film with a thickness of 1.6  $\mu\text{m}$  formed on the surface thereof and the  
- diameter thereof being 200 mm. As a result, the  
30 consumption of the inner wall of the chamber was about 7  $\mu\text{m}$ . In a conventional etching apparatus, the inner wall of the chamber is consumed about 50  $\mu\text{m}$  in the same condition. Therefore, the consumption of the inner wall

09827307.100401



of the chamber was able to be reduced to 1/7 by using the plasma etching apparatus according to the present embodiment.

It was found from the above-mentioned results that by applying a radio frequency electric power having a frequency the same as that applied to the first electrode 102 but having a different phase to the auxiliary electrode, the inner wall of the chamber was prevented from being sputtered and was prevented from being sputtered at most at the antiphase since the plasma potential was reduced.

Next, the amount of consumption of the auxiliary electrode 104 was measured by applying to the auxiliary electrode a radio frequency electric power having a frequency of 100 MHz which is higher than the frequency 13.56 MHz of the radio frequency electric power applied to the first electrode. FIG. 11 is a graph showing the results of measurement.

As shown in FIG. 11, by increasing the frequency of the radio frequency power supply 311 connected to the auxiliary electrode 104, the self-bias voltage generated in the auxiliary electrode 104 can be suppressed and an amount of consumption of the auxiliary electrode 104 due to sputtering can be reduced. Although the radio frequency electric powers of 13.56 MHz and 100 MHz were used in the measurement, the present invention is not limited to this combination, and a radio frequency electric power of about 27 MHz may be applied to the first electrode 102 and a radio frequency electric power of 60 MHz may be applied to the auxiliary electrode 104. Alternatively, radio frequency electric powers of 40 MHz and 80 MHz may be applied to the first electrode 102 and the auxiliary electrode 104, respectively. Although there

09827307-100401

are various frequencies of the radio frequency electric power applied to the first electrode 102 and the auxiliary electrode 104 as mentioned above, a higher frequency is preferable for the radio frequency applied to the auxiliary electrode 104.

As mentioned above, by increasing the frequency of the radio frequency power supply 311 connected to the auxiliary electrode 104, the self-bias voltage generated in the auxiliary electrode 104 can be suppressed, and the consumption of the auxiliary electrode 104 due to sputtering can be reduced.

Additionally, using the plasma etching apparatus shown in FIG. 1, a silicon substrate was etched 300 times by introducing a mixed gas of  $C_4F_8$ , carbon monoxide, oxygen, and xenon into the process chamber and setting the pressure to 5 Pa. The silicone substrate had a silicone oxidization film with a thickness of  $1.6 \mu m$  formed on the surface thereof and the diameter thereof was 200 mm. As a result measurement of the amount of consumption of eh auxiliary electrode 104, the amount of consumption was about 5 mm. Since the amount of consumption in a conventional etching apparatus is 65 mm, the amount of consumption was reduced to 1/13 of that of the conventional apparatus.

Next, the radio frequency electric power as investigated, which is applied to the auxiliary electrode and is able to make the self-bias potential most uniform by the position relationship (height relationship) between the surface of the first electrode 102 and the front surface 106 of the auxiliary electrode 104.

FIG. 12 is graph showing changes in the radio frequency electric power, which is applied to the auxiliary electrode and required to uniformize a self-bias

09827307.100401

potential according to the difference in the height between the upper surface of first electrode 102 and the upper surface 106 of the auxiliary electrode 104. When the height of the upper surface of the first electrode 102 and the height of the upper surface 106 of the auxiliary electrode 104 were equal to each other, the radio frequency electric power, which is applied to the auxiliary electrode and required in order to uniformize the self-bias potential, was 100 W. The radio frequency electric power applied to the auxiliary electrode and required to uniformize the self-bias potential increased as the difference in the height was increased, and the radio frequency electric power was 300 W when the height difference was 50 mm. Therefore, it was found that the radio frequency electric power applied to the auxiliary electrode required to uniformize the self-bias potential can be made the lowest when the height of the upper surface of the first electrode 102 and the upper surface 106 of the auxiliary electrode 104 were equal to each other.

FIG. 13 is an illustration showing the action of an electronic drift when the surface of the first electrode 102 is higher than the front surface 106 of the auxiliary electrode 104. FIG. 14 is an illustration showing the action of an electronic drift when the surface of the first electrode 102 is lower than the front surface 106 of the auxiliary electrode 104.

As shown in FIG. 13, in order to prevent the drift of electrons generated on the front surface 106 of the auxiliary electrode 104 from disappearing due to collision with the first electrode 102, the difference between the height of the surface of the first electrode 102 and the height of the position of the surface 106 of

09827307 100401

the auxiliary electrode 104 needs to be smaller than the cycloid radius of the electron drift. Moreover, in order to prevent the electron drift generated on the surface of the substrate 101 from disappearing due to collision with  
5 the auxiliary electrode 104, the difference between the height of the surface of the first electrode 102 and the height of the position of the front surface 106 of the auxiliary electrode 104 needs to be smaller than the cycloid radius of the electron drift.

10 Therefore, the self-bias potential can be equalized with a small radio frequency electric power by setting the height of the surface 106 of the auxiliary electrode 104 equal to the surface of the substrate 101 or setting the difference between the height of the front  
15 surface 106 of the auxiliary electrode 104 and the height of the surface of substrate 101 equal to or less than 2 mm.

Additionally, using the plasma etching apparatus according to the present embodiment, a silicon substrate was etched by introducing a mixed gas of  $C_4F_8$ , carbon  
20 monoxide, oxygen, and xenon into the process chamber and setting the chamber pressure to 5 Pa. The silicone substrate had a silicone oxidization film with a thickness of 1.6  $\mu m$  formed on the surface thereof, and the diameter was 200 mm. A radio frequency electric power of 1500 W  
25 was supplied to the first electrode 102 and a high frequency electric power of 100 W was supplied to the auxiliary electrode 104. As a result, the uniformity of the etching rate was  $\pm 2\%$ .

As explained above, according to the plasma  
30 processing apparatus of the present invention, uniformization of the density of the generated plasma with respect to the surface of the substrate and uniformization of the self-bias potential can be attempted without

09827307.100401

rotating the magnetic field applying means independently of the shape of the upper electrode and the distance thereof while maintaining the pressure distribution on the substrate uniform, and, thereby, the etching process  
5 without a charge up damage or the sputtering process which is uniform with respect to the substrate and does not generate a stress can be performed.

Additionally, a plasma processing apparatus having a high radio frequency electric power efficiency  
10 can be realizable by covering the surface of the auxiliary electrode by an insulating material.

Further, a plasma processing apparatus having a high radio frequency electric power efficiency can be realizable by equalizing the level of the surface of the  
15 substrate placed on the first electrode and the level of the front surface of the auxiliary electrode or setting the difference of the heights to less than  $\pm 2$  mm.

Additionally, a plasma processing apparatus with a small electric power, a small installation volume and a  
20 small magnetic field leakage can be realized by using a dipole magnet-ring as the magnetic field applying means.

Additionally, a plasma processing apparatus in which a chamber wall is prevented from being sputtered can be realized by setting a frequency  $f_1$  of a radio frequency  
25 applied to the first electrode and a frequency  $f_2$  of a radio frequency applied to the auxiliary electrode equal to each other and differentiating phases from each other.

Furthermore, a plasma processing apparatus in which a consumption of the auxiliary electrode is  
30 suppressed is realized by setting a frequency  $f_2$  of a radio frequency applied to the auxiliary electrode higher than a frequency  $f_1$  of a radio frequency applied to the first electrode ( $f_2 > f_1$ ).

09827307-100401  
TOP SECRET